(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
29 January 2004 (29.01.2004)

PCT

(10) International Publication Number
WO 2004/010212 A1

(51) International Patent Classification[7]: G02F 1/1337

(21) International Application Number:
PCT/KR2002/001782

(22) International Filing Date:
19 September 2002 (19.09.2002)

(25) Filing Language: Korean

(26) Publication Language: English

(30) Priority Data:
2002/42658 19 July 2002 (19.07.2002) KR

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(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

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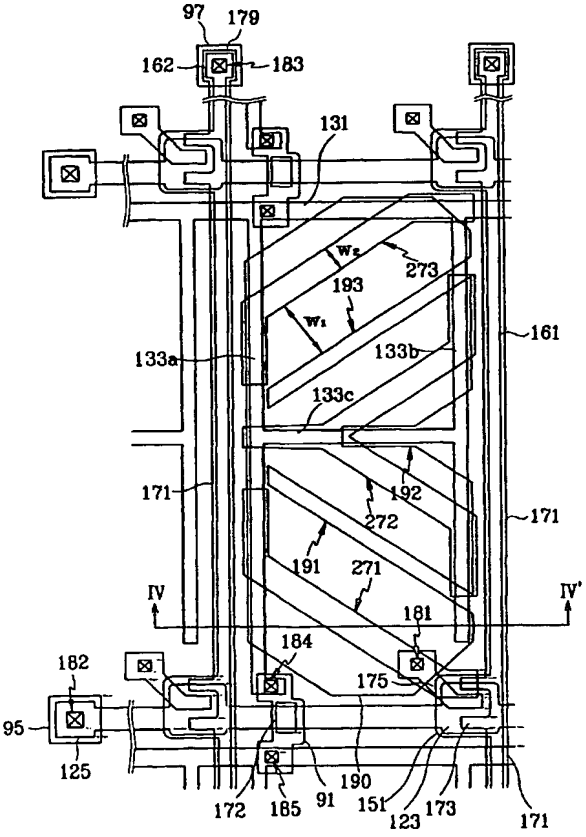
(54) Title: VERTICALLY ALIGNED MODE LIQUID CRYSTAL DISPLAY



(57) Abstract: A liquid crystal display is provided, which includes: a first insulating substrate; a gate line formed on the first insulating substrate; a gate insulating layer formed on the gate line; a data line formed on the gate insulating layer; a passivation layer formed on the data line; a pixel electrode formed on the passivation layer and a first cutout pattern; a second insulating substrate facing the first insulating substrate; and a common electrode formed on the second insulating substrate and having a second cutout pattern, wherein width of the domains is equal to or less than 30 microns.

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